

## P-Channel 200 V (D-S) MOSFET

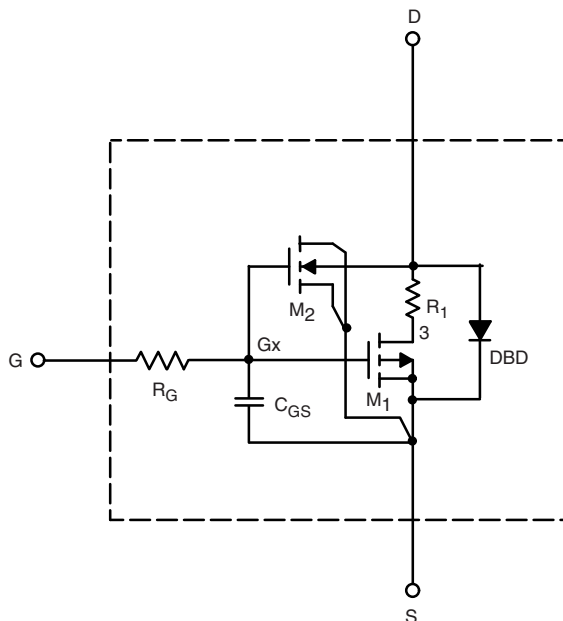
### DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the p-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to + 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage. A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

### SUBCIRCUIT MODEL SCHEMATIC

### CHARACTERISTICS

- P-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the - 55 °C to + 125 °C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics



### Note

- This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

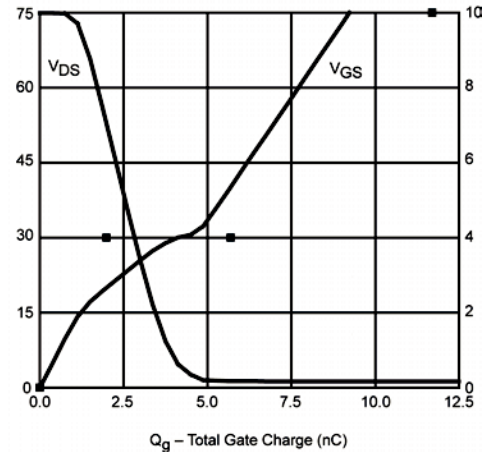
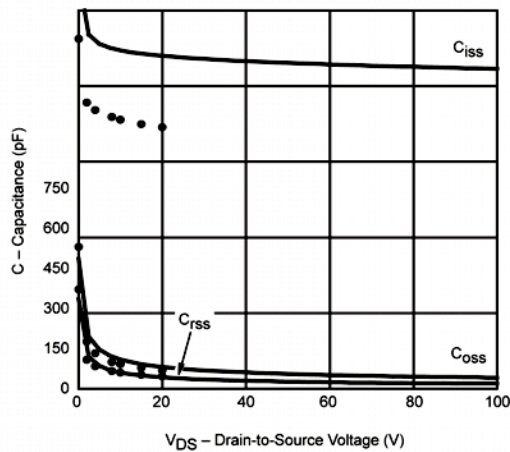
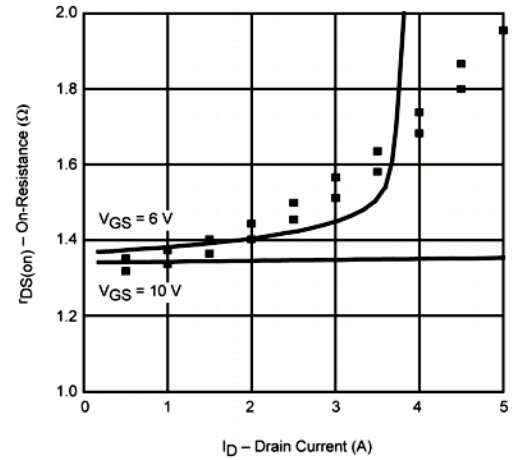
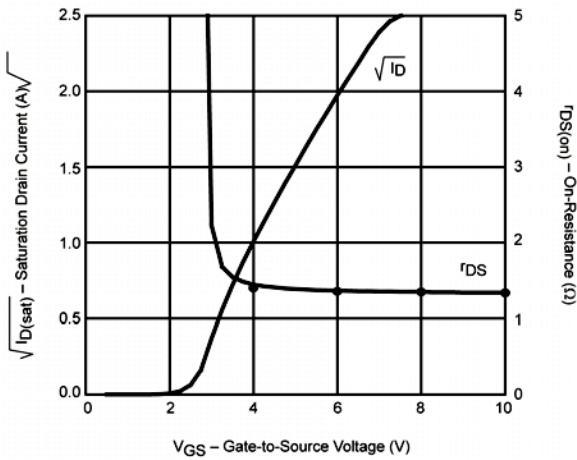
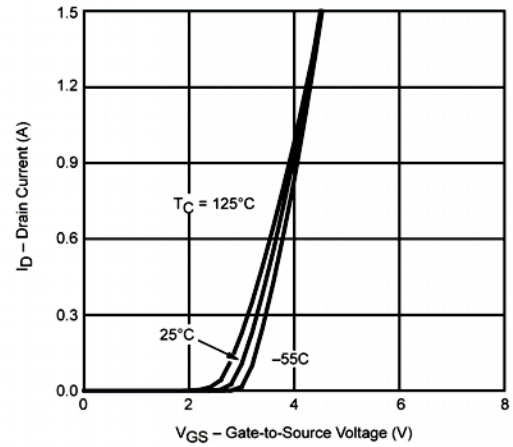
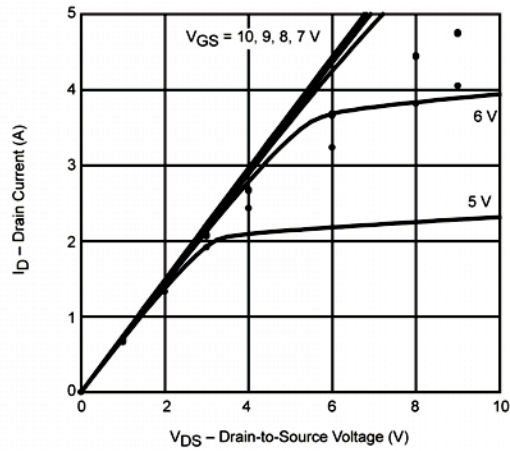


SPECIFICATIONS ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
<b>Static</b>					
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = -250\text{ }\mu\text{A}$	2.3	-	V
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = -5\text{ V}$ , $V_{GS} = -10\text{ V}$	7.3	-	A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$ , $I_D = -0.90\text{ A}$	1.34	1.34	$\Omega$
		$V_{GS} = -6\text{ V}$ , $I_D = -0.70\text{ A}$	1.37	1.37	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -10\text{ V}$ , $I_D = -0.90\text{ A}$	3	3.5	S
Diode Forward Voltage	$V_{SD}$	$I_S = -1\text{ A}$ , $V_{GS} = 0\text{ V}$	-0.78	-0.81	V
<b>Dynamic<sup>b</sup></b>					
Input Capacitance	$C_{iss}$	$V_{DS} = -50\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$	646	500	pF
Output Capacitance	$C_{oss}$		30	26	
Reverse Transfer Capacitance	$C_{rss}$		15	18	
Total Gate Charge	$Q_g$	$V_{DS} = -100\text{ V}$ , $V_{GS} = -10\text{ V}$ , $I_D = -1\text{ A}$	9.4	11.7	nC
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -100\text{ V}$ , $V_{GS} = -6\text{ V}$ , $I_D = -1\text{ A}$	6.4	7.8	
Gate-Drain Charge	$Q_{gd}$		2	2	
			3.7	3.7	

**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

## COMPARISON OF MODEL WITH MEASURED DATA ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)



### Note

- Dots and squares represent measured data.